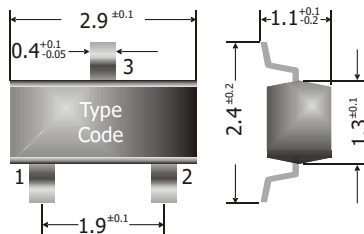


BAS16, BAW56, BAV70, BAV99, BAV199
SMD Small Signal Diodes
SMD Kleinsignal-Dioden
 $I_{FAV} = 215 \text{ mA}$
 $V_{F1} < 715 \text{ mV}$
 $T_{jmax} = 150^\circ\text{C}$
 $V_{RRM} = 85 \text{ V}$
 $I_{FSM} = 2 \text{ A}$
 $t_{rr1} < 4 \text{ ns}$

Version 2018-02-06

SOT-23
(TO-236)


Dimensions - Maße [mm]

Typical Applications
Signal processing, (High-speed)
Switching, Rectifying
Commercial grade ¹⁾
Typische Anwendungen
Signalverarbeitung, (Schnelles)
Schalten, Gleichrichten
Standardausführung ¹⁾
Features
BAV199: Extremely low leakage
BAS16, BAW56, BAV99, BAV70:
Very high switching speed
Compliant to RoHS, REACH,
Conflict Minerals ¹⁾
Besonderheiten
BAV199: Extrem niedriger Sperrstrom
BAS16, BAW56, BAV99, BAV70:
Sehr schnelles Schalten
Konform zu RoHS, REACH,
Konfliktmineralien ¹⁾
**Mechanical Data ¹⁾**

Taped and reeled

3000 / 7"

Weight approx.

0.01 g

Case material

UL 94V-0

Solder & assembly conditions

260°C/10s

Löt- und Einbaubedingungen

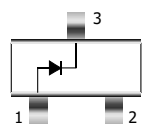
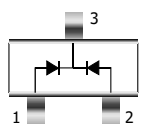
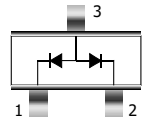
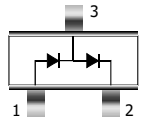
MSL = 1

Mechanische Daten ¹⁾

Gegurtet auf Rolle

Gewicht ca.

Gehäusematerial

BAS16  Single Diode Type Code 5D 1 = A 2 = n. c. 3 = C	BAV70  Common Cathode Type Code A4 1 = A1 2 = A2 3 = C1/C2
BAW56  Common Anode Type Code A1 1 = C1 2 = C2 3 = A1/A2	BAV99 BAV199  Series Connection Type Code A7 PX 1 = A1 2 = C2 3 = C1/A2

Maximum ratings ²⁾**Grenzwerte ²⁾**

Power dissipation (per device) – Verlustleistung (pro Bauteil)	P_{tot}	350 mW ³⁾
Maximum average forward current Dauergrenzstrom	single diode loaded – eine Diode belastet both diodes loaded – beide Dioden belastet	I_{FAV} 215 mA ³⁾ 125 mA ³⁾
Repetitive peak forward current – Periodischer Spitzenstrom	I_{FRM}	300 mA ³⁾
Non repetitive peak forward surge current Stoßstrom-Grenzwert	$t_p \leq 1 \text{ s}$ $t_p \leq 1 \text{ ms}$ $t_p \leq 1 \mu\text{s}$	I_{FSM} 0.5 A 1 A 2 A
Repetitive peak reverse voltage Periodische Sperrspannung	BAS16, BAW56, BAV99, BAV199 BAV70	V_{RRM} 85 V 100 V
Reverse voltage – Sperrspannung	DC	V_R 75 V
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur	T_j T_s	-55...+150°C -55...+150°C

¹ Please note the [detailed information on our website](#) or at the beginning of the data book

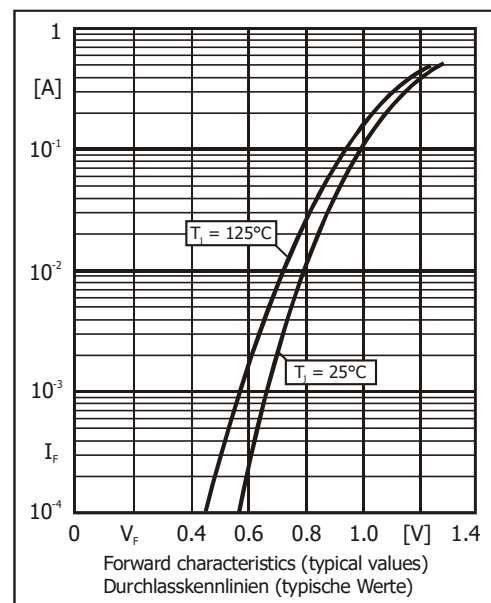
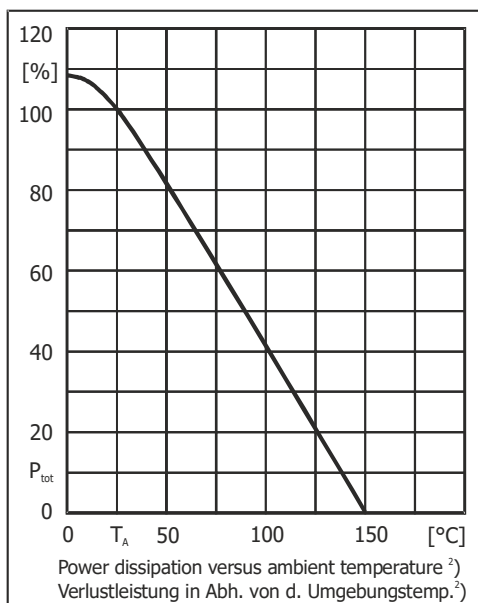
² Bitte beachten Sie die [detaillierten Hinweise auf unserer Internetseite](#) bzw. am Anfang des Datenbuches

³ $T_A = 25^\circ\text{C}$ and per diode, unless otherwise specified – $T_A = 25^\circ\text{C}$ und pro Diode, wenn nicht anders angegeben

³ Mounted on 3 mm² copper pads per terminal – Montage auf 3 mm² Kupferbelag (Löt pads) je Anschluss

Characteristics
Kennwerte

				BAS16, BAW56 BAV99	BAV70	BAV199
Forward voltage Durchlass-Spannung ¹⁾	$T_j = 25^\circ\text{C}$	$I_F =$ 1 mA 10 mA 50 mA 150 mA	V_F	< 715 mV < 855 mV < 1.0 V < 1.25 V	< 715 mV < 855 mV < 1.0 V < 1.25 V	< 900 mV < 1.0 V < 1.1 V < 1.25 V
Leakage current Sperrstrom ¹⁾	$T_j = 25^\circ\text{C}$	$V_R =$ 20 V 25 V 75 V	I_R	– < 30 nA < 1.0 μA	< 25 nA – < 2.5 μA	– – < 5 nA
	$T_j = 150^\circ\text{C}$	$V_R =$ 25 V 75 V	I_R	< 30 μA < 50 μA	< 30 μA < 50 μA	– < 80 nA
Junction capacitance Sperrschichtkapazität	$V_R = 0\text{ V}, f = 1\text{ MHz}$		C_T	typ. 2 pF		
Reverse recovery time Sperrverzögerung	$I_F = 10\text{ mA}$ über/through $I_R = 10\text{ mA}$ bis/to $I_R = 1\text{ mA}$		t_{rr}	< 4 ns	< 4 ns	< 3000 ns
Thermal resistance junction to ambient Wärmewiderstand Sperrschicht – Umgebung			R_{thA}	< 400 K/W ²⁾		



Disclaimer: See data book page 2 or [website](#)
Haftungsausschluss: Siehe Datenbuch Seite 2 oder [Internet](#)

- 1 Tested with pulses $t_p = 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
Gemessen mit Impulsen $t_p = 300\text{ }\mu\text{s}$, Schaltverhältnis $\leq 2\%$
- 2 Mounted on 3 mm² copper pads per terminal
Montage auf 3 mm² Kupferbelag (Lötpads) je Anschluss